

Description

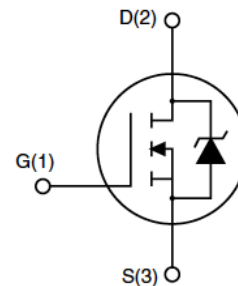
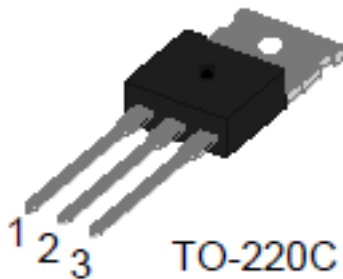
The SI010N10PG1 uses **Super Trench I** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

- $V_{DS} = 100V, I_D = 70A$
 $R_{DS(ON)} = 9m\Omega$ (typical) @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
SI010N10PG1	SI010N10PG1	TO-220-3L			5000

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	70	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	50	A
Pulsed Drain Current	I_{DM}	210	A
Maximum Power Dissipation	P_D	100	W
Derating factor		0.92	W/°C
Single pulse avalanche energy ^(Note 5)	E_{AS}	29	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	1.25	°C/W
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Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.0		2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	9	10	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =12A		10	14	mΩ
Dynamic Characteristics (Note 4)						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	2604	-	PF
Output Capacitance	C _{oss}		-	361	-	PF
Reverse Transfer Capacitance	C _{rss}		-	6.5	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =25A V _{GS} =10V, R _G =2.2Ω	-	20	-	nS
Turn-on Rise Time	t _r		-	5.0	-	nS
Turn-Off Delay Time	t _{d(off)}		-	51	-	nS
Turn-Off Fall Time	t _f		-	9	-	nS
Total Gate Charge	Q _g	V _{DS} =50V, I _D =25A, V _{GS} =10V	-	50	-	nC
Gate-Source Charge	Q _{gs}		-	6.55		nC
Gate-Drain Charge	Q _{gd}		-	12		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =30A	-		1.3	V
Diode Forward Current (Note 2)	I _S		-	-	70	A
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = 12A di/dt = 100A/μs (Note 3)	-	60	-	nS
Reverse Recovery Charge	Q _{rr}		-	106	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : T_J=25 °C, V_{DD}=40V, V_G=10V, L=0.5mH, R_G=25Ω

Typical Electrical and Thermal Characteristics

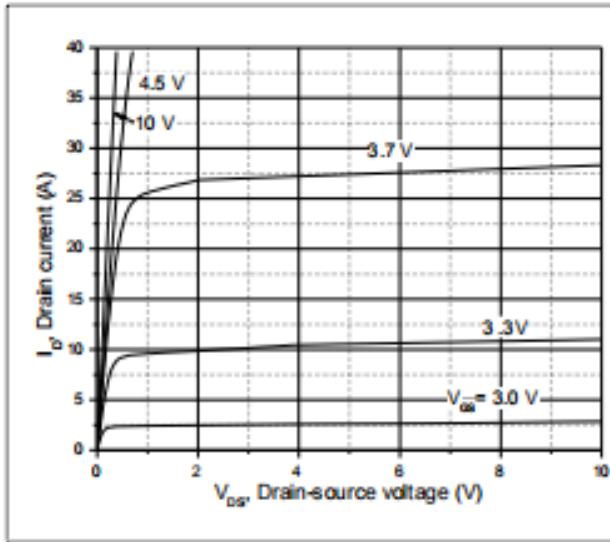


Figure 1, Typ. output characteristics

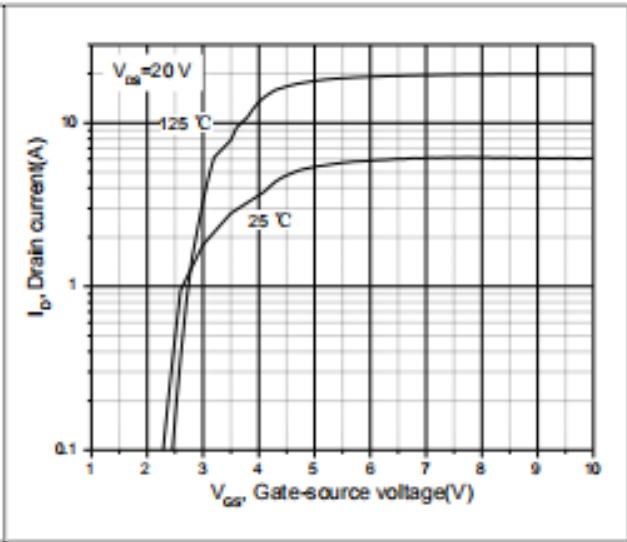


Figure 2, Typ. transfer characteristics

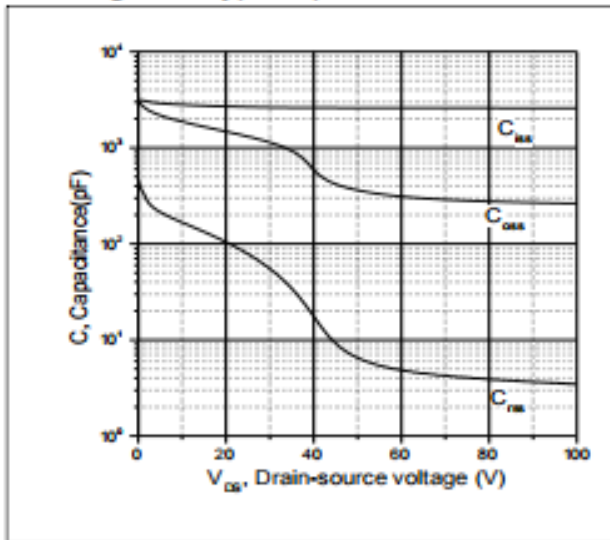


Figure 3, Typ. capacitances

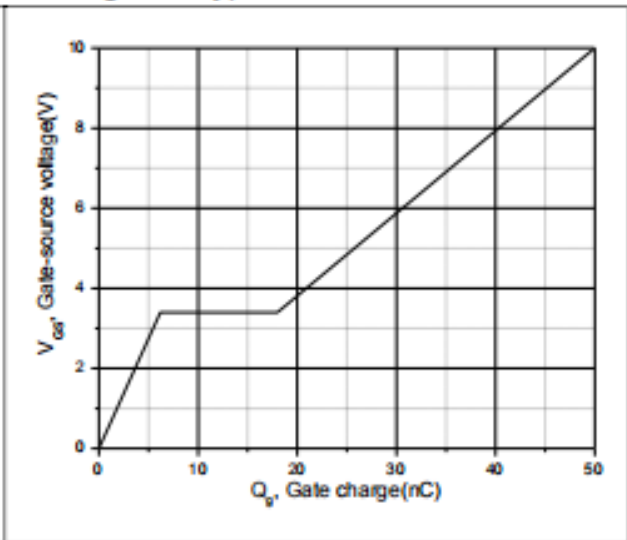


Figure 4, Typ. gate charge

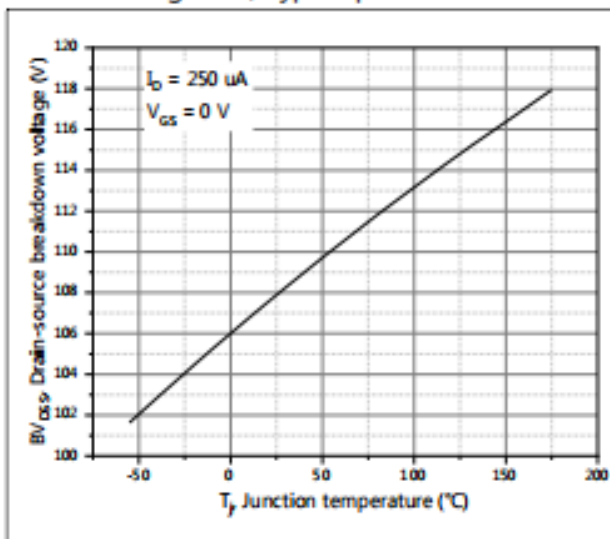


Figure 5, Drain-source breakdown voltage

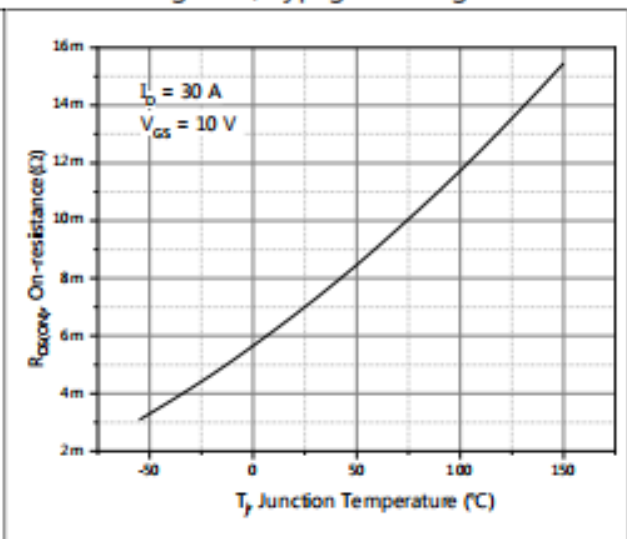


Figure 6, Drain-source on-state resistance

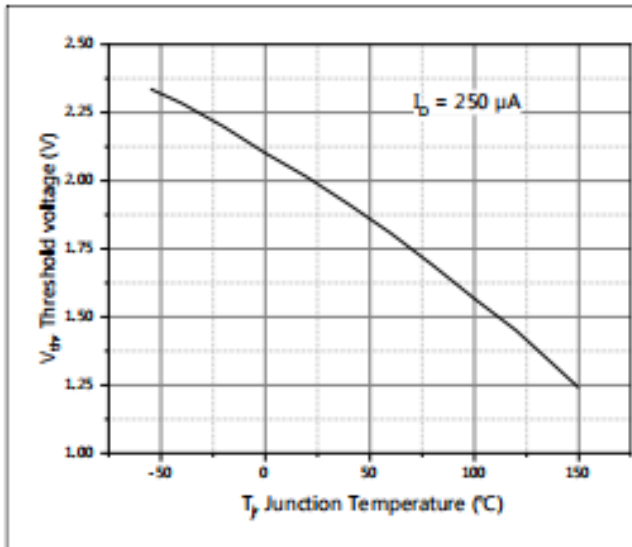


Figure 7, Threshold voltage

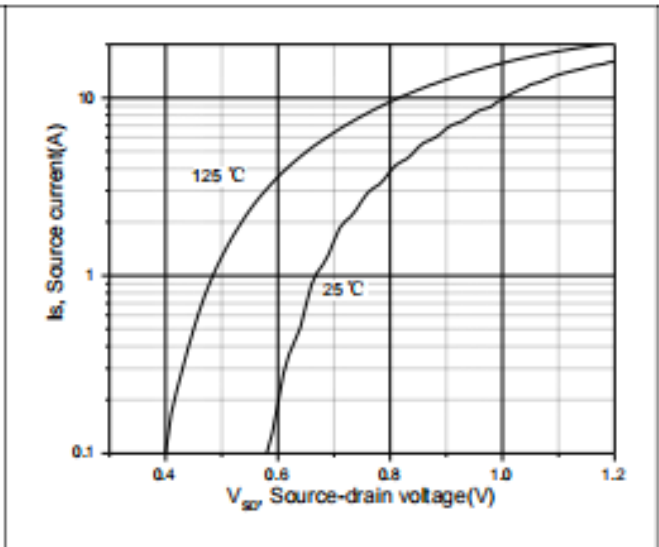


Figure 8, Forward characteristic of body diode

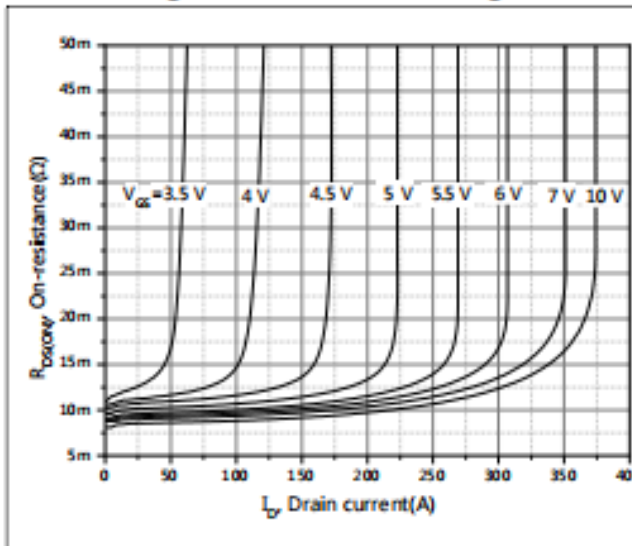


Figure 9, Drain-source on-state resistance

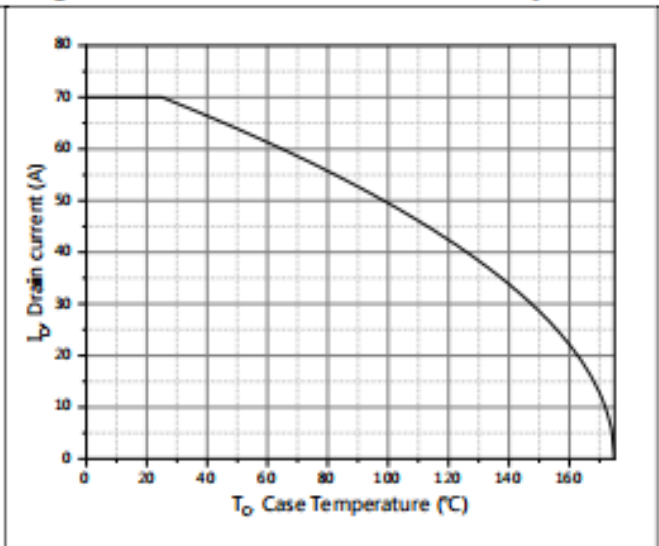


Figure 10, Drain current

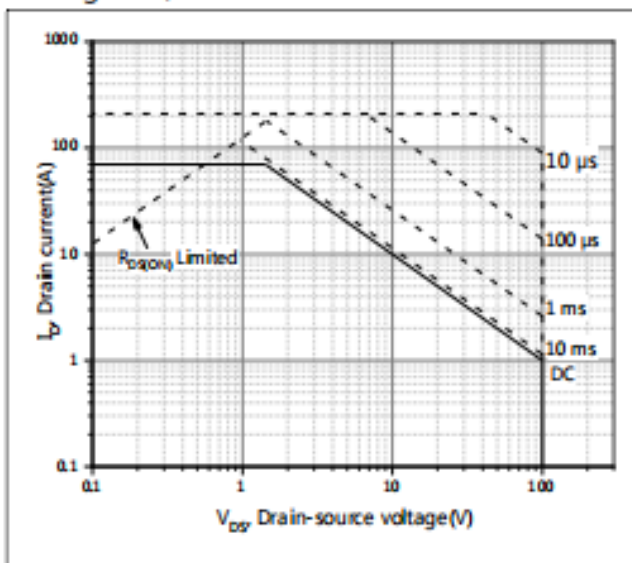


Figure 11, Safe operation area $T_C = 25 \text{ }^\circ\text{C}$

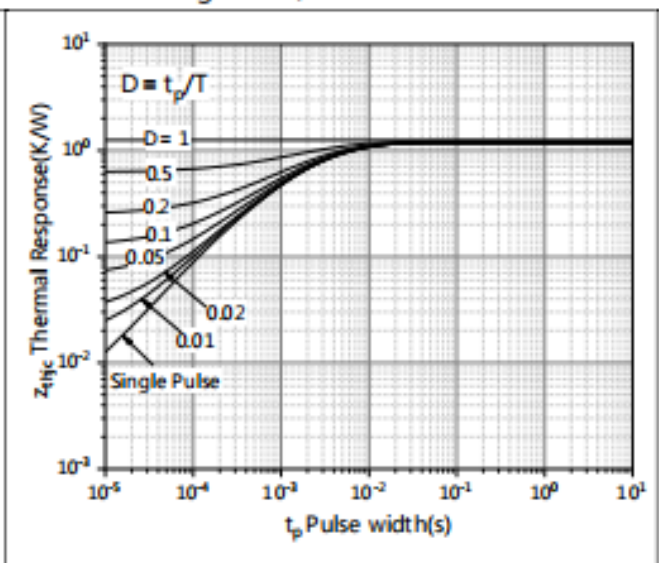
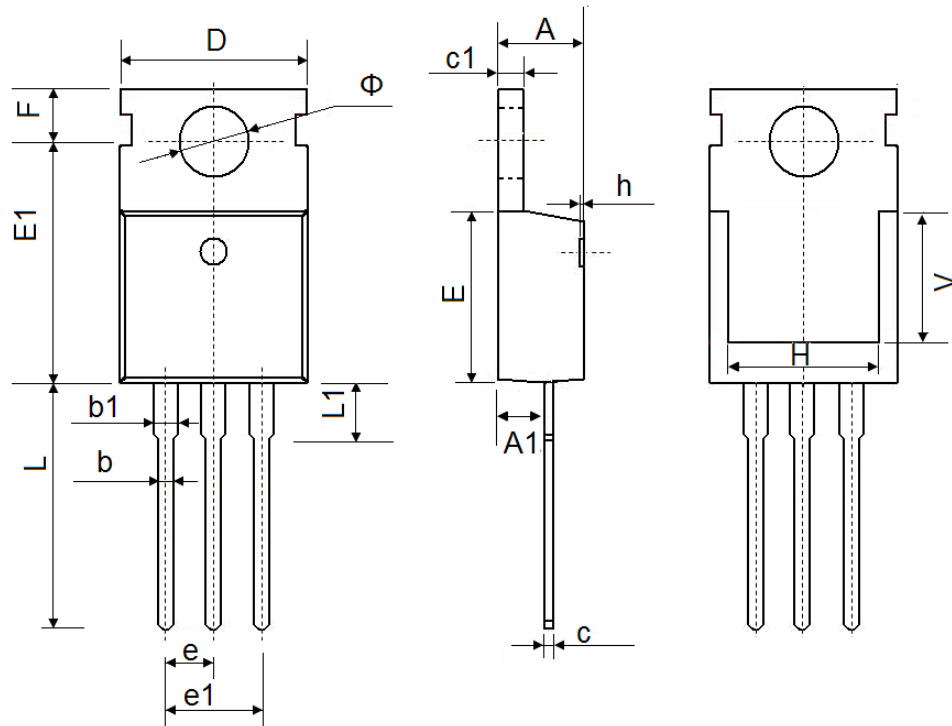


Figure 12, Max. transient thermal impedance

TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150